

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP02515K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

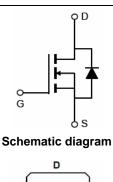
General Features

- V_{DS} =250V, I_D =15A $R_{DS(ON)}$ =200m Ω (typical) @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!





Marking and pin assignment



TO-252 -2Ltop view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02515K	NCEP02515K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	250	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I _D	15	Α
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	10.6	Α
Pulsed Drain Current	I _{DM}	60	Α
Maximum Power Dissipation	P _D	140	W
Derating factor		0.93	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	80	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$ C

Thermal Characteristic

Thermal Résistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.1	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	250	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =250V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			•
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =15A	-	200	220	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =15A	15	-	-	S
Dynamic Characteristics (Note4)			•			•
Input Capacitance	C _{lss}	\\ 405\\\\ 0\\	-	475		PF
Output Capacitance	C _{oss}	V _{DS} =125V,V _{GS} =0V,	-	34		PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	1.2		PF
Switching Characteristics (Note 4)			•			•
Turn-on Delay Time	t _{d(on)}		-	4	-	nS
Turn-on Rise Time	t _r	V_{DD} =125V, RL=8 Ω	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	10	-	nS
Turn-Off Fall Time	t _f		-	2	-	nS
Total Gate Charge	Qg	\/ 405\/ L 45A	-	8.9	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =125V,I _D =15A,	-	3.3	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	2.5	-	nC
Drain-Source Diode Characteristics	1			l		•
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =15A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	15	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = I_S$	-	25	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	110	-	nC

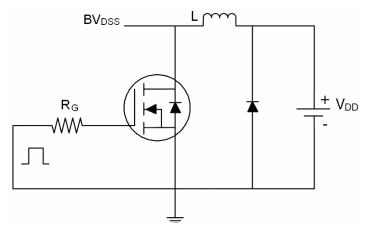
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

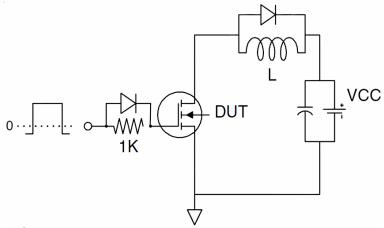


Test Circuit

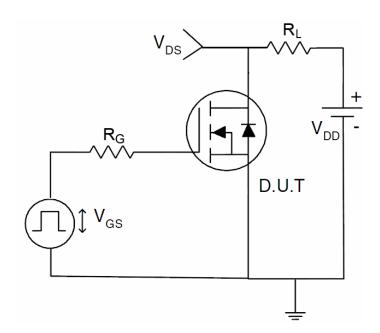
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

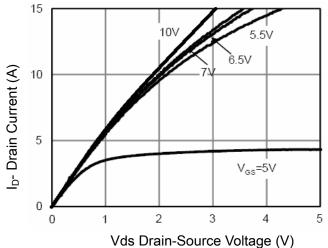


Figure 1 Output Characteristics

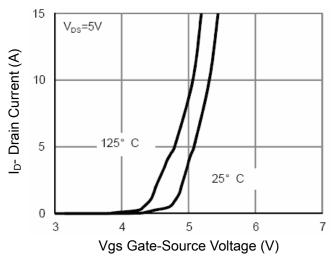


Figure 2 Transfer Characteristics

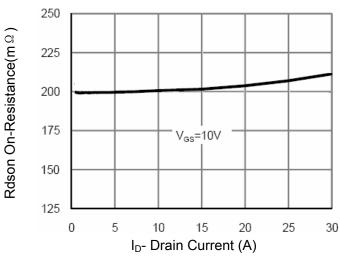


Figure 3 Rdson- Drain Current

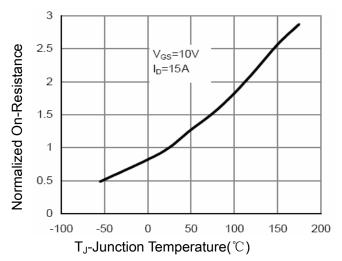


Figure 4 Rdson-Junction Temperature

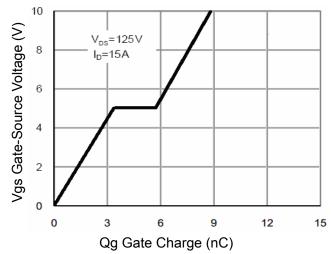


Figure 5 Gate Charge

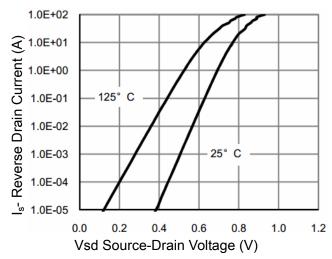


Figure 6 Source- Drain Diode Forward



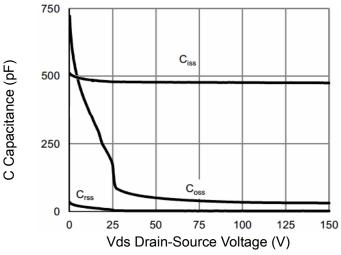


Figure 7 Capacitance vs Vds

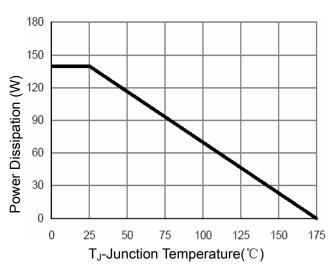


Figure 9 Power De-rating

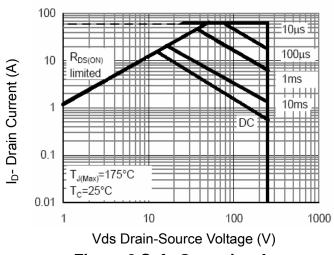


Figure 8 Safe Operation Area

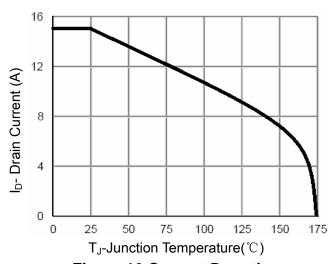
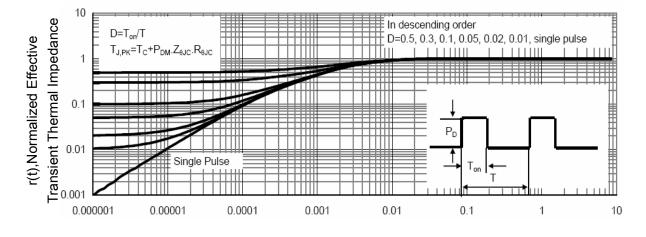


Figure 10 Current De-rating

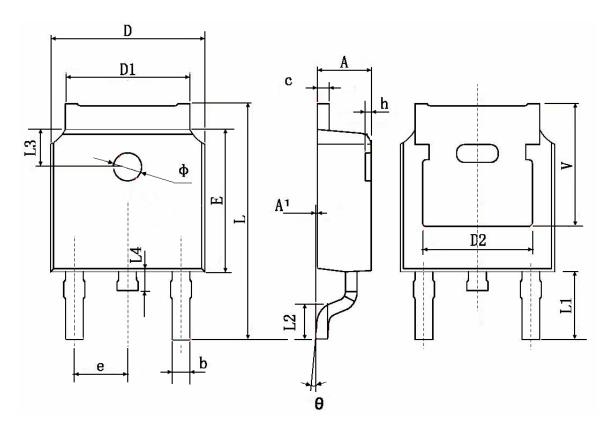


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Compleal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.8	330 TYP.	0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.90	0 TYP. 0.114 T		YP.	
L2	1.400	1.700	0.055	0.067	
L3	1.60	00 TYP. 0.063 TYF		TYP.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.35	5.350 TYP. 0.211 TYP.		TYP.	

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NCEP02515K

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